

Wavelength range	Type	Technology	Electrodes
Infrared	Planar	InGaAs/InP	P (anode) up

	typ. dimensions in μm					
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Miscellaneous Parameters

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.196	mm^2
Operating temperature range		T_{amb}	-40 to +125	$^\circ\text{C}$
Temperature coefficient of I_D	$T = -40 \dots 120^\circ\text{C}$	$T_C(I_D)$	7.4	%/K

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 10 \text{ mA}$	V_F		0.8		V
Breakdown voltage ²⁾	$I_R = 10 \mu\text{A}$	V_R	5			V
Sensitivity range at 10 %	$V_R = 0 \text{ V}$	λ	800		1750	nm
Spectral bandwidth at 50 %	$V_R = 0 \text{ V}$	$\Delta\lambda_{0,5}$		680		nm
Responsivity at 1300 nm ¹⁾	$V_R = 0 \text{ V}$	S_λ		0.9		A/W
Dark current	$V_R = 5 \text{ V}$	I_D		250	1000	pA
Shunt resistance	$V_R = 10 \text{ mV}$	R_{SH}	0.5	1.0		G Ω
Noise equivalent power	$\lambda = 1300 \text{ nm}$	NEP		1.1×10^{-14}		W/ $\sqrt{\text{Hz}}$
Specific detectivity	$\lambda = 1300 \text{ nm}$	D^*		4.0×10^{12}		$\text{cm} \cdot \sqrt{\text{Hz}} \cdot \text{W}^{-1}$
Junction capacitance	$V_R = 0 \text{ V}$	C_J		45		pF

¹⁾measured on bare chip on TO-18 header

²⁾for information only

Note: All measurements carried out with JENOPTIK Polymer Systems equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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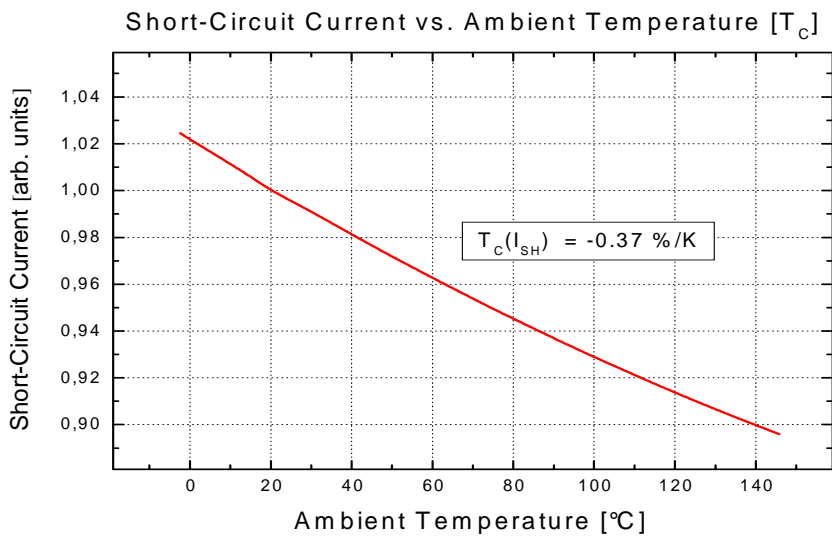
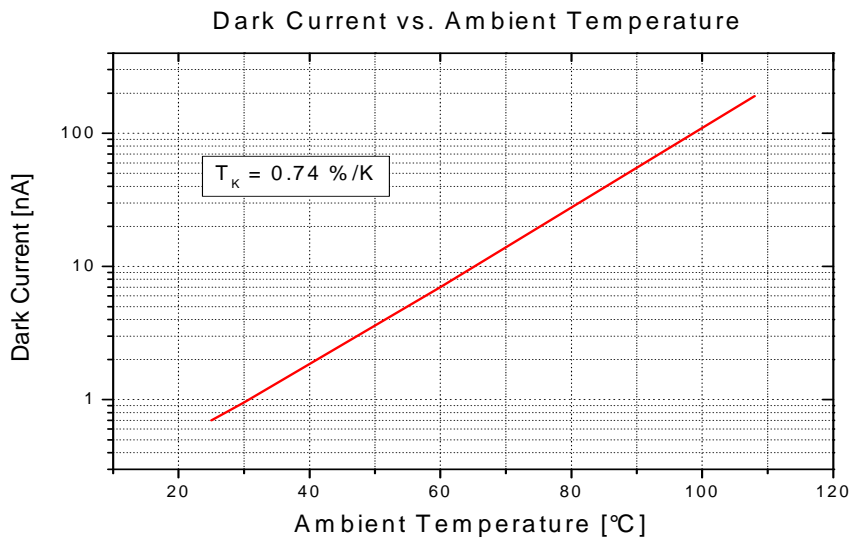
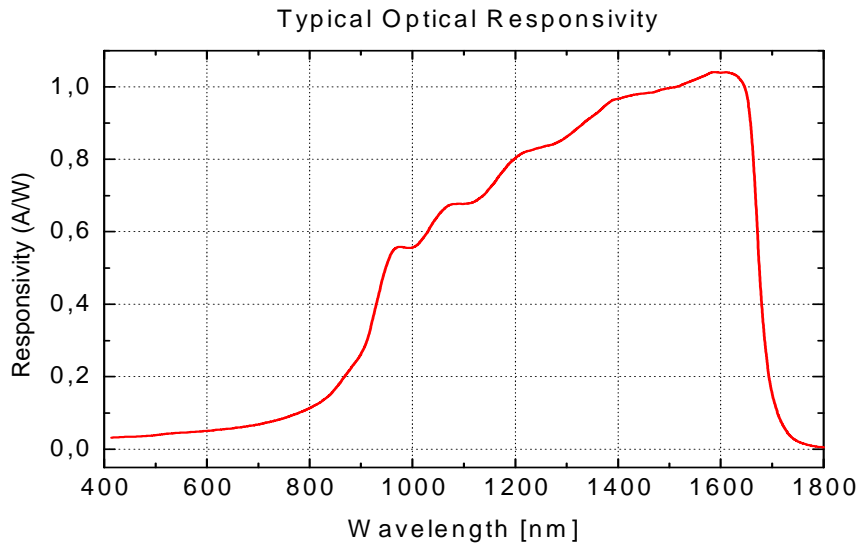
Labeling

Type	Typ. I_D [pA]	Typ. S_λ [A/W]	Lot N°	Quantity
EPC-1300-0.5-1				

Packing: Chips on adhesive film with wire-bond side on top

Environmental		Symbol	Min	Typ	Max	Unit
Storage Temperature	on Blue Tape	T_{STG}	15		30	°C
Storage Relative Humidity	on Blue Tape	RH_{STG}	40		75	% RH
Storage Time	on Blue Tape	t_{STG}			1	year

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